

Deformation Electron-Phonon Coupling in Disordered Semiconductors and Nanostructures

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We study the electron-phonon relaxation (dephasing) rate in disordered semiconductors and low-dimensional structures. The relaxation is determined by the interference of electron scattering via the deformation potential and elastic electron scattering from impurities and defects. We have found that in contrast to the destructive interference in metals, which results in the Pippard ineffectiveness condition for the electron-phonon interaction, the interference in semiconducting structures substantially enhances the effective electron-phonon coupling. The obtained results provide an explanation to energy relaxation in silicon structures.

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Elastic electron scattering from impurities and defects drastically changes the electron-electron and electron-phonon (e-ph) interaction and modifies temperature dependencies of the relaxation/dephasing rate. As a result of diffusive motion of electrons, the electron-electron interaction is significantly enhanced in bulk and low-dimensional conductors [1]. Recent theoretical [2, 3] and experimental [2, 4] studies have shown that the piezoelectric e-ph coupling is also enhanced in semiconductors with short electron mean free path. Effects of disorder on the deformation e-ph coupling are more complicated. In impure metals, the deformation coupling originates from "pure" electron-phonon scattering, electron scattering from vibrating impurities, and various interference processes. If electron scatterers vibrate in the same way as host atoms, the destructive interference of scattering mechanisms [5, 6] results in the Pippard ineffectiveness condition [7], which means suppression of the e-ph relaxation. In this case, at low temperatures the relaxation rate modifies from T^3 -dependence in the pure materials to T^4 -dependence in the impure metals. However, even small amount of static scatterers (e.g. tough boundaries) or incomplete drag of impurities and defects increases the e-ph relaxation [8]. Disorder-suppressed relaxation is observed in disordered metallic films [9, 10], while alloys commonly demonstrate the disorder-enhanced relaxation with T^2 -dependence of the relaxation rate [11].

Recently, there has been significant interest to the electron relaxation in disordered semiconductors and structures, where the electron relaxation is determined by electron-phonon scattering via the deformation potential (DP). The relaxation rate has been measured in Si crystals containing (Sb)-layer [12, 13] and in Si films [14]. Experimental results, including T^4 -dependence of the electron relaxation rate, were associated with the

Pippard ineffectiveness condition, obtained for metals. However, in the temperature ranges investigated in Refs. [12, 13] and [14], DP is strongly screened and the relaxation rate in pure 2D and quasi-2D structures follows to T^5 -dependence [15, 16]. Therefore, the ineffectiveness would result in the T^6 , rather than the T^4 -dependence.

It is not surprising that the theory developed for metals [5, 6, 7] fails to describe semiconductors. Indeed, DP in metals and semiconductors has different nature [17]. In metals, DP is associated with electron gas compressibility, while in semiconductors this contribution is negligible due to small carrier concentrations. DP in semiconductors results mainly from a shift of the conduction-band edge under the deformation, while in metals such contribution is small because of strong screening. It is important that DP has different tensor structures in metals and semiconductors [17, 18], and this difference clearly manifests itself even in weakly disordered conductors [19]. Here we show that the tensor structure of DP plays a crucial role in kinetics of strongly disordered conductors: in contrast to the destructive interference in metals, the electron-phonon-impurity interference in semiconducting structures substantially enhances e-ph coupling.

Here we report results on the e-ph relaxation in disordered bulk semiconductors, two-dimensional electron structures, and multi-channel one-dimensional conductors interacting with 3D phonons. Effects of disorder are described by the dimensionless parameter ql , where q is the characteristic momentum transferred to the electron due to e-ph scattering, $l = v_F \tau$ is the electron mean free path due to scattering from impurities, v_F is the Fermi velocity. In the impure limit, $ql \ll 1$, a phonon interacts with an electron that diffuses in the interaction region, $L \approx l = q^{-1}$. In bulk conductors, q is the wavevector of a thermal phonon, $q_T = T/u$ (u is the sound velocity),

and the crossover to the impure limit occurs at $T = u$.

In low-dimensional conductors, the characteristic momentum q is determined by the phonon wavevector component q_k , which is parallel to the conductor. In two-dimensional systems, q_k is of the order of q_T and, as well as in bulk semiconductors, the crossover is described by the parameter $q_T l = T l = u$. In 1D channels the transferred momentum q_k is $(u = v_F) q_T$ and effects of disorder become important at significantly higher temperatures, $T \gg q_T l < 1$. The same parameter T describes modification of the electron-electron interaction [1].

Investigating the electron energy relaxation, we focus our attention on the time scale much longer than the electron momentum relaxation time. In this time domain, electron-phonon kinetics is described by the angle-averaged electron and phonon distribution functions, n and N . We consider interference processes, which are characterized by the momentum transfer much smaller than the Fermi momentum. In this case, the interference of electron-phonon and electron-impurity scattering is taken into account by the electron self-energy diagram shown in Fig. 1. The corresponding electron-phonon collision integral is [6, 8]

$$I = 4 \int \frac{dq d!}{(2)^4} \frac{1}{j_n^R j} = D^R(q;!) < \frac{n}{1 - n} \quad (1)$$

$$N_! n (1 - n_+) (1 + N_!) (1 - n) n_+; \quad (1)$$

where $D^R(q;!)$ is the phonon Green function

$$D^R(q;!) = (! - !_q + i0)^{-1} + (! + !_q + i0)^{-1}; \quad (2)$$

$= D_0(q, e) = (2q)^{1-2}$ is the vertex of the electron-phonon interaction, D_0 is the constant of DP, and e is the phonon polarization vector.

In the collision integral I , n is an integral over the impurity-averaged electron Green functions [6],

$$n = \frac{1}{n} \int \frac{dp}{(2)^n} G^A(p;) G^R(p + q; + !)$$

$$= \begin{cases} \frac{\arctan(q_l)}{(q_l)} & n = 3, \\ \frac{1}{1 + (q_k l)^2} & n = 2, \\ \frac{1}{(1 - i!) + (q_k l)^2} & n = 1, \end{cases} \quad (3)$$

where n is the two-spin electron density of states in n -dimensional electron system. We limited our consideration by the condition $q_l > u = v_F \cdot 10^2$, which allows us to put $! = 0$ in $_3$ and $_2$.

The screening of DP is described by the dielectric function $\epsilon(q;!)$. Further calculations show that in the 3D and 2D electron systems the characteristic frequencies $! \ll T$ are small compared with D_0^2 (D is the diffusion coefficient). In this limit the dielectric function is

$$\epsilon(q) = \frac{1 + (q_3 = q)^2}{1 + (q_2 = q_k)^2}; \quad \begin{matrix} \frac{2}{3} = 4 e^2 \epsilon_3 & 3D; \\ \frac{2}{2} = 2 e^2 \epsilon_2 & 2D. \end{matrix} \quad (4)$$

For 1D conductors we should take into account the dynamical character of electron screening. If $q_k r \ll 1$ (r is the conductor radius), the dielectric function is

$$\epsilon = 1 + e^2 \int \ln \frac{1}{(q_k r)^2} \frac{(q_k l)^2}{(q_k l)^2} \frac{1}{(i!)^2} : \quad (5)$$

The e-ph relaxation rate is calculated as a variation of the collision integral $\frac{1}{\tau_{e-ph}} = \frac{1}{\tau_{ph}} = n_e$. In equilibrium, $N_! = N_!^{eq}(T)$ and $n = n^{eq}(T)$, and the relaxation rate of electrons at the Fermi surface ($= 0$) is

$$\frac{1}{\tau_{e-ph}} = 4 \int \frac{dq}{(2)^3} \frac{1}{j_n^R j} (N_!^{eq} + n_!^{eq}) < \frac{n(!_q)}{1 - n(!_q)} : \quad (6)$$

We also calculate the heat flux from hot electrons with the temperature to phonons with the temperature T . The heat flux may be presented through the energy control function $F(T)$ as

$$P(;T) = n \frac{d}{dT} I(;T) = F() - F(T); \quad (7)$$

$$F(T) = 4 \int \frac{dq}{(2)^3} \frac{1}{j_n^R j} !^2 N_!^{eq} < \frac{n(!_q)}{1 - n(!_q)} : \quad (8)$$

First we calculate the relaxation rate in a bulk semiconductor. Substituting $_3$ (Eq. 3) and $_3(q)$ (Eq. 4) into Eq. 6 we find

$$\frac{1}{\tau_{e-ph}} = \frac{D_0^2 T^3}{u^2 (p_F u)^2} F(q_T l; q_T = _3); \quad (9)$$

$$F(y; z) = \int_0^1 dx x^2 \frac{xy \arctan(xy)}{xy \arctan(xy)} \frac{(xz)^2}{(xz)^2 + 1} (N_x^{eq} + n_x^{eq}); \quad (10)$$

These formulas in limiting cases are summarized in Tab. I. In the pure limit, $T l = u \ll 1$, we reproduce well-known results [17]: in the case of weak screening, $T > u_3$, the relaxation rate is proportional to T^3 ; for screened DP, $T < u_3$, the relaxation rate changes as T^7 . In the impure limit the relaxation rate is proportional to $T^2 = 1$ for unscreened DP and to $T^6 = 1$ for the screened DP. Thus, contrary to the Pippard ineffectiveness condition in metals [5, 6, 7], the relaxation rate in semiconductors is enhanced by a factor of $u = (T l)$ due to elastic electron scattering. The energy control function may be estimated as $F(T) \sim C_e T = \tau_{e-ph}$, where C_e is the electron heat capacity. In Tab. I we present $F(T)$ with exact coefficients, because measurements of $F(T)$ are widely used to obtain D_0 .

Now we consider the e-ph relaxation in two-dimensional electron gas. Using Eqs. 3 and 4, we find that the relaxation rate (Eq. 6) may be presented as

$$\frac{1}{\tau_{e-ph}} = \frac{D_0^2 T^3}{2^2 v_F u^4} (q_T l; q_T = _2); \quad (11)$$

$$\langle y; z \rangle = \int_0^1 dx x^2 \int_0^1 d\phi \frac{xy}{1 + (xy \sin \phi)^2} \frac{(xz)^2 \sin^3 \phi}{(xz \sin \phi + 1)^2} (N_x^{\text{eq}} + n_x^{\text{eq}}): \quad (12)$$

These formulas in limiting cases are summarized in Tab. II. In the pure limit, we reproduce well-known results [15]. In the temperature range $T \ll T_D$, where DP is weakly screened, the relaxation rate is proportional to T^3 ; for strongly screened DP the relaxation rate changes as T^5 . In the impure limit, in the case of weak screening, the relaxation rate is proportional to $T^2 \ln T$ and inversely proportional to l . At low temperatures, where DP is strongly screened, the relaxation rate is proportional to $T^4 = 1$. Thus, in heterostructures elastic electron scattering significantly enhances the e-ph interaction.

Finally, we consider the e-ph interaction in the multichannel 1D system. Channels may be associated with wires, shells, and electron subbands. Variations of the multichannel model are applied to one-dimensional organic conductors, CuO-chains in high- T_c superconductors, and multi-wall carbon nanotubes [20]. For simplicity we consider identical channels and neglect the Coulomb interaction between channels. We suggest that electrons are scattered between channels and interchannel scattering prevails over backscattering in the same channel, so the system is in the conducting state. Electron-phonon scattering keeps an electron in the same channel and, therefore, it is screened by electrons in this channel. Using Eqs. 3 and 6, we find that without screening the relaxation rate in the pure conductor is given by

$$\frac{1}{\tau_{\text{e-ph}}} = \frac{7}{8} \frac{(3) D_0^2 T^3}{v_F u^4}: \quad (13)$$

Calculating the integrant in Eq. 6 in the general case, note that for a 1D conductor $q_k = q \cos \phi = q_x$ (ϕ is the angle between q and a wire) and within the logarithmic accuracy the integral over the direction of q is given by

$$\int_0^1 dx \frac{(q_l x)^2}{[(1 - 2\epsilon_1 \ln q_x r) (q_l x)^2 + (\frac{1}{2} \epsilon_1^2 + \frac{1}{2} \epsilon_1^2)]^2} = \frac{1}{2q_l (1 - 2\epsilon_1 \ln q_r)^{3/2}} = \frac{2}{8!} \frac{1}{1}, \quad (14)$$

Eq. 14 shows that the crossover to the impure limit is described by the parameter ϵ_1 , which is of the order of T^{-1} . In the impure limit, $T \ll T_D$, the characteristic value of the transferred momentum q_r is $l^{-1} \epsilon_1 = (1 + \epsilon_1^2)^{-1/2}$, $l^{-1} \epsilon_1 = (1 + \epsilon_1^2)^{-1/2}$. In this case, the relaxation rate and energy control function for the one-dimensional multichannel conductor are

$$\frac{1}{\tau_{\text{e-ph}}} = \frac{3}{64} \frac{8}{2} \frac{D_0^2 T^5}{v_F u^4} \quad (5=2)$$

$$F(T) = \frac{105}{128} \frac{(9=2)}{2} \frac{D_0^2 T^9}{v_F u^4}: \quad (15)$$

As seen from Eq. 15, screening substantially changes values of $\tau_{\text{e-ph}}$ and $F(T)$, but just weakly affects the temperature dependencies. Compare Eqs. 13 and 15, we find that in the impure limit the electron-phonon interaction is enhanced by the factor of $l = T^{-1}$.

The electron-phonon-impurity interference in metals and semiconductors may be qualitatively understood in the following way. First, elastic electron scattering effectively averages DP over the Fermi surface. Second, the diffusive motion holds an electron in the interaction region and increases the interaction time. In metals the Fermi surface average of the deformation potential equals to zero [17, 18]. As a result of this averaging the effective e-ph vertex is substantially decreased (see Ref. [6]). In metals this effect prevails over the modification of the interaction time and strongly suppresses the e-ph relaxation. In semiconductors, DP weakly depends on the electron momentum and the DP tensor is usually approximated by a constant. Therefore, elastic scattering in semiconductors enlarges the interaction time, which in turn enhances the e-ph relaxation.

Recently the e-ph relaxation rate has been directly measured in 2D electron gas in Si with MBE-grown Sb-layer [12, 13]. Because of lack of the theory for semiconducting materials and structures, the observed T^4 -dependence was associated with the Pippard concept of the ineffectiveness of the e-ph interaction. According to our results, the T^4 -dependence in 2D structures originates from disorder-enhanced screened DP coupling (see Tab. II). Analogous data with T^4 -dependence have been obtained in heavily doped quasi-two-dimensional Si in s at subKelvin temperatures [14]. Note, that e-ph relaxation rate is often evaluated from the electron dephasing rate. Such data also give evidence in favor of significant enhancement of e-ph coupling in disordered semiconductors. For example, in 3D SiP layers with $l \approx 5$ nm the relaxation time at 4.2 K was found to be ≈ 10 ps [21] which is significantly shorter than that in pure materials.

To conclude, we calculate the e-ph relaxation rate in disordered semiconductors (Eq. 9, Tab. 1), two-dimensional (Eq. 11, Tab. 2) and one-dimensional (Eq. 15) semiconducting structures. Our results show that the e-ph relaxation is strongly enhanced due to disorder. The research was supported by the ONR and MRCAF grants.

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FIG. 1: Electron self-energy diagram. Wavy line stands for e-ph scattering, a dotted line stands for to elastic electron scattering from random potential, and a straight line stands for the electron Green function.

TABLE I: Electron-phonon energy relaxation time and energy control function in a bulk semiconductor.

| | | T > u ₃ (weak screening) | | T < u ₃ (strong screening) | |
|--------------------|--|---|--|--|---|
| | | T > u=1 | T < u=1 | T > u=1 | T < u=1 |
| τ_{e-ph}^{-1} | | $\frac{7}{4} (3) \frac{D_0^2}{u^2} \frac{T^3}{(p_F u)^2}$ | $\frac{3}{4} \frac{D_0^2}{u^2} \frac{T^2}{p_F^2 \hbar u}$ | $\frac{5715}{8} (7) \frac{D_0^2}{u^2} \frac{T^7}{p_F^2 \frac{4}{3} u^6}$ | $\frac{3}{4} \frac{D_0^2}{u^2} \frac{T^6}{p_F^2 \frac{4}{3} \hbar u^5}$ |
| F(T) | | $6 (5) \frac{D_0^2}{u^2} \frac{T^5}{(p_F u)^2}$ | $\frac{4}{10} \frac{D_0^2}{u^2} \frac{T^4}{p_F^2 \hbar u}$ | $10080 (9) \frac{D_0^2}{u^2} \frac{T^9}{p_F^2 \frac{4}{3} u^6}$ | $\frac{4}{5} \frac{D_0^2}{u^2} \frac{T^8}{p_F^2 \frac{4}{3} \hbar u^5}$ |

TABLE II: Electron-phonon energy relaxation time and energy control function in two-dimensional electron structures.

| | | T > u ₂ (weak screening) | | T < u ₂ (strong screening) | |
|--------------------|--|---|---|--|--|
| | | T > u=1 | T < u=1 | T > u=1 | T < u=1 |
| τ_{e-ph}^{-1} | | $\frac{7}{4} (3) \frac{D_0^2 T^3}{v_F u^4}$ | $\frac{D_0^2 T^2}{\hbar v_F u^3} \ln \frac{T}{2u}$ | $\frac{93}{8} (5) \frac{D_0^2 T^5}{\frac{2}{2} v_F u^6}$ | $\frac{2}{4} \frac{D_0^2 T^4}{\frac{2}{2} \hbar v_F u^5}$ |
| F(T) | | $\frac{6}{v_F u^4} (5) \frac{D_0^2 T^5}{2}$ | $\frac{2}{15} \frac{D_0^2 T^4}{\hbar v_F u^3} \ln \frac{T}{2u}$ | $\frac{90}{\frac{2}{2} v_F u^6} (7) \frac{D_0^2 T^7}{2}$ | $\frac{8}{63} \frac{D_0^2 T^6}{\frac{2}{2} \hbar v_F u^5}$ |

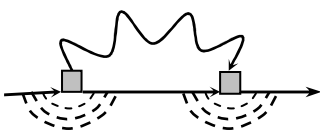


Fig.1

